# **BTI Status**

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#### Overview of the electronics layout of a chamber



## **DT Chamber Electronics layout**



Trigger R/O minicrate services 990901- signals cables not sketched

## DT Chamber Trigger layout

MB1 Trigger/Readout and Control Electronics

Server & Control unit **128 ch.**  $\phi$  unit 128 ch. **()** unit **128 ch.** θ unit 128 ch.  $\theta$  unit D A B A WATER WATER POWER SUPPLY WATER WATER 250 250 250 Α 250E I/O side 1670 From the LO side: • I/O board: power decoupling, SC connectors, ... MB1 chamber electronics mini-crate layout three 128 channels Phi\_TRB: BTI, TRACO and TSS • Server and Control board: chamber services, SC interface From the I/O side: power supply decoupling two 128 channels units for the θ view one 128 channels unit for the θ view one 128 channels unit for the φ view Each PCBthasSernae anch Cantrohengit bours for control signals distribution. Chamber \$1899.4128 shared units af or a the bleievonnecting the ROB to the FE boards (A). Each TRB Sends thank to the berver board using a dedicated flat cable (B). Each ROB is connected to the Sector Collector via a dedicated serial link (C). Each 128 channel unit has four flat cables connected to the Front-ends (A). one flat cable for the Trigger connection with the Server (B). Monitoring and control purposes, and connections to the Sector Collector for trigger one twisted pair for the Readout connection with the Sector Collector(C) The Server and Control unit has connections with the front-ends for settings and monitoring (D),

Trigger connections with the Sector Collector (E) and connections with the Master Slow Control in the control room (F). MB1ELv11t, Padova 14 nov

# DT Chamber PHI Trigger board



## PHI\_TRB

- 128 trigger channels
- 3.3V 10W power supply
- 40MHz clock
- > 8 BTIM + 4 TRACO + 1 TSS
- > single PECL clock input @ 40MHz
- > low skew clock distribution
- > temperature sensor
- > JTAG circuitry
- > low-drop regulator with over-voltage
  and over-current protection
- > on/off control and isolation switches

• DT Chamber THETA Trigger board



### THETA\_TRB

- 128 trigger channels
- 3.3V 10W power supply
- 40MHz clock

#### > 8 BTIM

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# BTI Multi-Chip Module

## LTCC substrate

- 4 BTI dies
- 3.3V 0.85W
- 80 I/O
- 40MHz and 80MHz clocks







#### WIRE SIGNAL INPUTS 80MHz Input Shapers Register • Register • X 9 Register • Register **4** Counter 40MHz Register ┥ Register X 32 Pattern Patter Logic #1 Register 4 32 Priority/Quality Encoder Priority H/L K,X Ш Logic MUX Select Register **«** Register WCOMP LTS Register MUX s Output TRG Register Filter Register Register < Register **4** Control Logic 6bit Parallel – Prog – R/W – Strb 3bit K,X H/L TRG JTAG →JTAG port

05/12/00

Input signals sampling and shaping at 80MHz

Track pattern detection and impact parameters calculation

Pattern selection

Angular filter and LTS logic

Control logic

## BTI: Documents

- Overview and performances of chamber trigger:
  - "Design and Simulations of the Trigger Electronics for the CMS Muon Barrel Chambers", Ist Workshop on Electronics for LHC Experiments, 1995.

#### FPGA prototype test:

- "Beam Test Results of a FPGA Prototype of a Front-end Trigger Device for CMS Muon Barrel Chambers", IInd Workshop on Electronics for LHC Experiments, 1996.
- "Efficiency studies of the front-end trigger device of the muon drift tubes for the CMS detector at LHC", NIM A 398, 1997.

#### Full performance prototype test:

- "Local Track Reconstruction for the First Level Trigger in the CMS Muon Barrel Chambers", IVth Workshop on Electronics for LHC Experiments, 1998.
- "Test results of the ASIC front-end trigger prototypes for the muon barrel detector of CMS at LHC", NIM A 438, 1999.
- "Current knowledge of BTI performance in magnetic field", CMS Note 2000/044.



# BTI Performance: efficiency

Efficiency at normal incidence for different synchronization acceptance windows





BTI acceptance	LTS	%H out of tim	e %Louto
	<b>C C</b>	2 00	251 00

# • BTI Performance: efficiency

Efficiency and noise versus track incidence angle



Figure 11

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Figure 12

# • BTI Performance: efficiency

Efficiency for offerent configurations 98.38 98.38

Table 1 - BTI performance for different synchronizatio

BTI acceptar	IdeTS	HTRG fracti	ofATRG fracti	ominefficie	ncy
Standard	off	84.0%	15.6%	0.3%	
Standard	on	85.1%	13.6%	1.3%	
Minimum	on	70.7%	28.2%	1.1%	
Maximum	on	84.8%	13.8%	1.4%	

Table 2 - Efficiency figures for the tested configuration

HTRG only on BTI 6	5.1%
HTRG on BTI 6 and HTRG on BTI 5	4.4%
HTRG on BTI 6 and LTRG on BTI 5	74.08
LTRG only on BTI 6	10.1%

## BTI Performance: bx identification

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Synchronization ra	ngens	±4ns	±бns	±8ns	±10ns	±12ns		
HTRG fraction	84.38	\$ 83.						
LTRG fraction	14.58	: 15.	RX		∃ffi⁄	rian	icy and	nnica
Efficiency	98.88	s 98.			-		icy and	110130

Table 1 - BTI performance for different synchronization acceptance windc

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BE	ac	ce	ptar	dets	HTRG	fra	icti	o <b>p</b> ŢŖG	Ēf	<del>ra</del> et:	ofine	Eficie	ncy	
Sta	nda	rd		off	84.	.0%		1	. (	5%	0	.3%		
Sta	nda	rd		on	85.	.1%		1500	8.0	58	1	.3%		
Min	imur	n		on	70.	.7%		<sup>1250</sup> 2	<b>a</b> .:	28	1	<u>.1</u> %		
4Mgg	imu	n		on	84.	.8%		10001		8%	1	.4%		
3000 E 750 E														
2000 <sup>T</sup>	apt	e	2 -	Effic	iency :	tig	ure	$s tor_{500}$	Eti	ie te	sted	conti	gurati	ons
1000	-							250	E				_	
HTR	€o	nl	y, on	BTI	6			0	5	. 15.	181.			
HTR	ලී ං	n <sup>2</sup>	BTI	f and	HTRG	on <sup>1</sup>	<sup>0</sup> BTI	5 (	)	<sup>2</sup> 4.	4\$ <sup>4</sup>	6	8 1	0
HTNumberent HERGoodpertextent BTI 5 Number of ETRGs per event														
LTRG only on BTI 6							10.	1%	1					
LTR	Gο	n	BTI	6 and	HTRG	on	BTI	5		0.	48			
LTR	Gο	n	BTI	6 and	LTRG	on	BTI	5		5.	98			



	Figure 13		
BTI acceptance	LTS	%H out of tim	e %L out of time
Standard	off	3.0%	351.2%
Standard	on	3.1%	148.2%
Minimum	on	1.1%	175.6%
Maximum	on	4.1%	165.3%

Table 4 - Average fraction of out of time triggers

05/12/00	%HTRG	%LTRG	Inefficie	nty out of t	imeL out of t	ime
No Radiatio	n84.0%	15.6%	0.3%	3.0%	351.2%	
Radiation	83.0%	16.6%	0.5%	2.5%	800.0%	
10 Hz/Cm						



Output time slot



## • BTI Performance: position measurement

### A ccuracy of track position measurement



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## BTI Performance: angle measurement

### Accuracy of track angle measurement



# BTI Performance: magnetic field



## BTI Performance: gamma rays background

#### Gamma rays background affects track position accuracy



Gamma rate = 10Hz/cm<sup>2</sup>

With gamma rays background

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F	BTI acceptance a	nce: gamma 1	avs backen	<b>BUNT</b> out of	
	Standard	off	3.0%	351.2%	
	Stan Gamma ray	148.2%			
		175.6%			
	Maximum	on	4.1%	165.3%	

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Radiation	83.0%	16.6%	0.5%	2.5%	800.0%	
IU HZ/CM						

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Table 5 - Comparison between performance without radiation and m

#### VIII. RESULTS SUMMARY

Results of the various tests are collected in Table 3 considering only the worst result for each device. We quote a 90% confidence level upper limit of the SEU cross section for all the integrated circuits which experienced no failure. The error in the SRAM SEU cross section is the squared sum of statistical and systematical

error. The latter one is due to the uncertainty of the total

[3] D.L. Oberg et al., IEEE Trans. On Nucl. Science, vol.43, No.6, Dec 1996

[4] P.J. Griffin et al., IEEE Trans. On Nucl. Science, vol.44, No.6, Dec 1997

[5] E. Normand, IEEE Trans. On Nucl. Science, vol.45, No.6, Dec 1998

[6] K. Johansson et al., IEEE Trans. On Nucl. Science, vol.45, No.6, Dec 1998 O PLANCE [7] J. W. Meadows, NIM. A324(1993)239.

neutron flux and is dominating our calculation. The Mean Time Between Failures is computed for the whole barrel muon detector, considering the numb chip used in the electronics layout. W BTI chips and few hundred pieces of t Meutron tolerance

D.L. Smith et al.,NIM A241(1985)507.

l., Advances in Neutron Capture Therapy,

l, Rad. Prot. Dos., Vol. 70, p. 559 (1997)

Table 3: SEU cross section and expected mean time between failures in the whole CMS muon barrel detector due to neutrons of different energy. We considered 500 n/cm<sup>2</sup> of thermal neutrons, 20 n/cm<sup>2</sup> with  $3 < E_n < 10$  MeV and 30 n/cm<sup>2</sup> with  $E_n > 10$  MeV.

	SE	EU cross section (cm	n <sup>2</sup> )	Mean Time Between Failures (hours)			
Device	Thermal	LNL	UCL	Thermal	LNL	UCL	
LD reg	$< 1.38 \mathrm{x} 10^{-10}$	$< 1.40 \mathrm{x} 10^{-11}$	$< 1.00 \mathrm{x} 10^{-12}$	< 64	< 15587	< 147892	
μΡ	$< 1.38 \mathrm{x} 10^{-10}$	< 1.40x10 <sup>-11</sup>	3.85x10 <sup>-11</sup>	< 385	< 95340	<mark>23088</mark>	
FLASH	$< 1.38 \mathrm{x} 10^{-10}$	$< 1.46 \mathrm{x} 10^{-12}$	$< 1.00 \mathrm{x} 10^{-12}$	< 385	< 91101	< 474734	
SRAM	(1.13±0.2)x10 <sup>-9</sup>	(7.03±0.2)x10 <sup>-10</sup>	$(1.03\pm0.2)$ x10 <sup>-8</sup>	<mark>23.5</mark>	<mark>1263</mark>	<mark>23</mark>	
EPROM	$< 1.38 \mathrm{x} 10^{-10}$	< 1.61x10 <sup>-11</sup>	$< 1.00 \mathrm{x} 10^{-12}$	< 385	< 83043	< 474734	
Optolink	$< 1.38 \mathrm{x} 10^{-10}$	$< 1.43 \mathrm{x} 10^{-11}$	$< 1.00 \mathrm{x} 10^{-12}$	< 385	< 93231	< 474734	
ASIC TSS	$< 2.68 \mathrm{x} 10^{-10}$	$< 9.46 \times 10^{-12}$		< 33	< 32225		
ASIC BTI	$< 1.75 \mathrm{x} 10^{-10}$	< 1.31x10 <sup>-11</sup>	$< 1.00 \mathrm{x} 10^{-12}$	< 1.5	< 507	< 4436	

No measurable degradation was observed after  $10^{12}$  n/cm<sup>2</sup>. No SEE were observed.





# BTI: Project Status

- BTI and DT chamber prototypes tested:
  - with muon beams and cosmic rays
  - with muon beams and radiation background (GIF)
  - with muon beams in high magnetic fields
- BTI tests in radiation background:
  - 10krad in gamma cell (2krad/minute)
  - thermal neutrons up to  $10^{10} \text{ n/cm}^2$
  - fast neutrons from reactor (Prospero) up to  $10^{11}$  n/cm<sup>2</sup>
  - fast neutrons (< 10MeV) from d-Be reaction up to  $2x10^{12}$  n/cm<sup>2</sup>
  - fast neutrons (< 60 MeV) from p-Be reaction up to  $10^{12} \text{ n/cm}^2$

Functional behaviour and performance are fully satisfactory.

After irradiation tests up to the reported levels no degradation in the electrical or functional characteristics was measured. No SEE was observed.

## BTI: Project status and future developments

#### Status and known problems:

- The ATMEL foundry in Europe has been closed. Only 1400 dies are still available from the first prototyping batch. The next batch could be produced by ATMEL in USA after a new prototyping phase and with 30 weeks of mask processing time.
- BTIM prototypes with LTCC substrate have low yield, about 40%.

#### *Future developments:*

- The BTI/BTIM tender must start as soon as possible to account for the unexpected delay needed by ATMEL to start chip production. A new prototyping batch could be received within mid 2001 placing the order for BTI production in December 1999.
- In order to gain time for BTIM production the tender must be anticipated and the 1400 available dies must be used for further prototyping.
- BTIM production schedule:
  - 50 pcs by September 2001
  - 950 pcs by December 2001
  - 5 lots of 2300 pcs from March 2002 to June 2003.